

DATA SHEET

74LVC1G00

Single 2-input NAND gate

Product specification
Supersedes data of 2002 Nov 15

2004 Sep 07

Single 2-input NAND gate

74LVC1G00

FEATURES

- Wide supply voltage range from 1.65 V to 5.5 V
- High noise immunity
- Complies with JEDEC standard:
 - JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - JESD8B/JESD36 (2.7 V to 3.6 V).
- ± 24 mA output drive ($V_{CC} = 3.0$ V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- ESD protection:
 - HBM EIA/JESD22-A114-B exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V.
- Specified from -40 °C to $+85$ °C and -40 °C to $+125$ °C.

DESCRIPTION

The 74LVC1G00 is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS compatible TTL families.

Input can be driven from either 3.3 V or 5 V devices. These features allow the use of these devices in a mixed 3.3 V and 5 V environment.

Schmitt trigger action at all inputs makes the circuit tolerant for slower input rise and fall time.

This device is fully specified for partial power-down applications using I_{off} . The I_{off} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC1G00 provides the single 2-input NAND function.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25$ °C; $t_r = t_f \leq 2.5$ ns.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t_{PHL}/t_{PLH}	propagation delay inputs A, B to output Y	$V_{CC} = 1.8$ V; $C_L = 30$ pF; $R_L = 1$ k Ω	3.3	ns
		$V_{CC} = 2.5$ V; $C_L = 30$ pF; $R_L = 500$ Ω	2.2	ns
		$V_{CC} = 2.7$ V; $C_L = 50$ pF; $R_L = 500$ Ω	2.8	ns
		$V_{CC} = 3.3$ V; $C_L = 50$ pF; $R_L = 500$ Ω	2.2	ns
		$V_{CC} = 5.0$ V; $C_L = 50$ pF; $R_L = 500$ Ω	1.8	ns
C_I	input capacitance		5	pF
C_{PD}	power dissipation capacitance per buffer	$V_{CC} = 3.3$ V; notes 1 and 2	14	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total switching outputs;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

2. The condition is $V_I = \text{GND}$ to V_{CC} .

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FUNCTION TABLE

See note 1.

INPUT		OUTPUT
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

Note

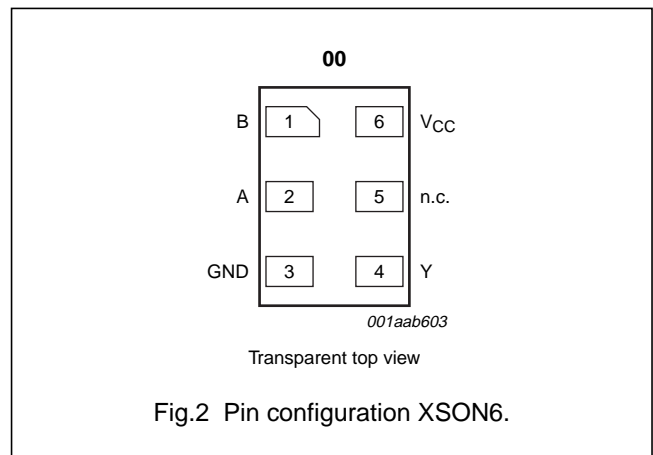
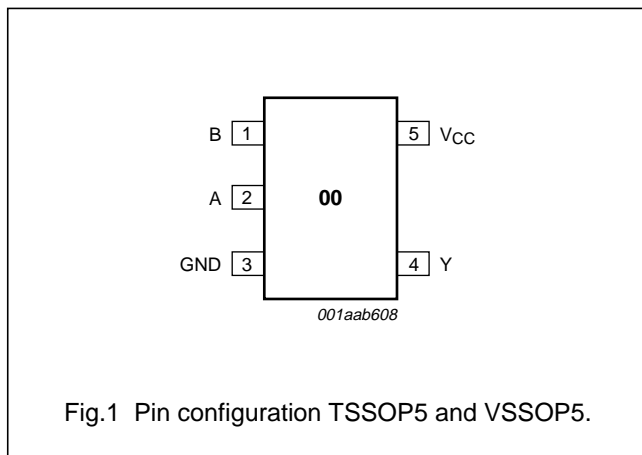
- H = HIGH voltage level;
L = LOW voltage level.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE					
	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING
74LVC1G00GW	-40 °C to +125 °C	5	SC-88A	plastic	SOT353	VA
74LVC1G00GV	-40 °C to +125 °C	5	SC-74A	plastic	SOT753	V00
74LVC1G00GM	-40 °C to +125 °C	6	XSON6	plastic	SOT886	VA

PINNING

PIN (TSSOP5, VSSOP5)	PIN (XSON6)	SYMBOL	DESCRIPTION
1	1	B	data input B
2	2	A	data input A
3	3	GND	ground (0 V)
4	4	Y	data output Y
-	5	n.c.	not connected
5	6	V _{CC}	supply voltage



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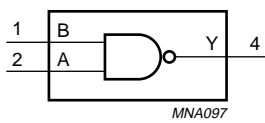


Fig.3 Logic symbol.

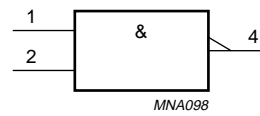


Fig.4 IEE/IEC logic symbol.

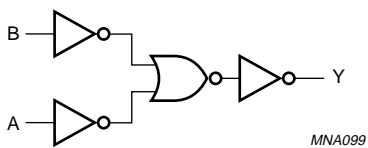


Fig.5 Logic diagram.

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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage		1.65	5.5	V
V_I	input voltage		0	5.5	V
V_O	output voltage	active mode	0	V_{CC}	V
		$V_{CC} = 0$ V; Power-down mode	0	5.5	V
T_{amb}	operating ambient temperature		-40	+125	°C
t_r, t_f	input rise and fall times	$V_{CC} = 1.65$ V to 2.7 V	0	20	ns/V
		$V_{CC} = 2.7$ V to 5.5 V	0	10	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage		-0.5	+6.5	V
I_{IK}	input diode current	$V_I < 0$ V	-	-50	mA
V_I	input voltage	note 1	-0.5	+6.5	V
I_{OK}	output diode current	$V_O > V_{CC}$ or $V_O < 0$ V	-	±50	mA
V_O	output voltage	active mode; notes 1 and 2	-0.5	$V_{CC} + 0.5$	V
		Power-down mode; notes 1 and 2	-0.5	+6.5	V
I_O	output diode current	$V_O = 0$ V to V_{CC}	-	±50	mA
I_{CC}, I_{GND}	V_{CC} or GND current		-	±100	mA
T_{stg}	storage temperature		-65	+150	°C
P_D	power dissipation per package	for temperature range from -40 °C to +125 °C	-	250	mW

Notes

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. When $V_{CC} = 0$ V (Power-down mode), the output voltage can be 5.5 V in normal operation.

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DC CHARACTERISTICS

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP. ⁽¹⁾	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = -40 °C to +85 °C							
V _{IH}	HIGH-level input voltage		1.65 to 1.95	0.65 × V _{CC}	–	–	V
			2.3 to 2.7	1.7	–	–	V
			2.7 to 3.6	2.0	–	–	V
			4.5 to 5.5	0.7 × V _{CC}	–	–	V
V _{IL}	LOW-level input voltage		1.65 to 1.95	–	–	0.35 × V _{CC}	V
			2.3 to 2.7	–	–	0.7	V
			2.7 to 3.6	–	–	0.8	V
			4.5 to 5.5	–	–	0.3 × V _{CC}	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 100 μA	1.65 to 5.5	–	–	0.1	V
		I _O = 4 mA	1.65	–	–	0.45	V
		I _O = 8 mA	2.3	–	–	0.3	V
		I _O = 12 mA	2.7	–	–	0.4	V
		I _O = 24 mA	3.0	–	–	0.55	V
		I _O = 32 mA	4.5	–	–	0.55	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = -100 μA	1.65 to 5.5	V _{CC} - 0.1	–	–	V
		I _O = -4 mA	1.65	1.2	–	–	V
		I _O = -8 mA	2.3	1.9	–	–	V
		I _O = -12 mA	2.7	2.2	–	–	V
		I _O = -24 mA	3.0	2.3	–	–	V
		I _O = -32 mA	4.5	3.8	–	–	V
I _{LI}	input leakage current	V _I = 5.5 V or GND	5.5	–	±0.1	±5	μA
I _{off}	power OFF leakage current	V _I or V _O = 5.5 V	0	–	±0.1	±10	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0 A	5.5	–	0.1	10	μA
ΔI _{CC}	additional quiescent supply current per pin	V _I = V _{CC} - 0.6 V; I _O = 0 A	2.3 to 5.5	–	5	500	μA

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SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP. ⁽¹⁾	MAX.	UNIT
		OTHER	V _{CC} (V)				
T_{amb} = -40 °C to +125 °C							
V _{IH}	HIGH-level input voltage		1.65 to 1.95	0.65 × V _{CC}	–	–	V
			2.3 to 2.7	1.7	–	–	V
			2.7 to 3.6	2.0	–	–	V
			4.5 to 5.5	0.7 × V _{CC}	–	–	V
V _{IL}	LOW-level input voltage		1.65 to 1.95	–	–	0.35 × V _{CC}	V
			2.3 to 2.7	–	–	0.7	V
			2.7 to 3.6	–	–	0.8	V
			4.5 to 5.5	–	–	0.3 × V _{CC}	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} I _O = 100 μA	1.65 to 5.5	–	–	0.1	V
		I _O = 4 mA	1.65	–	–	0.70	V
		I _O = 8 mA	2.3	–	–	0.45	V
		I _O = 12 mA	2.7	–	–	0.60	V
		I _O = 24 mA	3.0	–	–	0.80	V
		I _O = 32 mA	4.5	–	–	0.80	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} I _O = -100 μA	1.65 to 5.5	V _{CC} - 0.1	–	–	V
		I _O = -4 mA	1.65	0.95	–	–	V
		I _O = -8 mA	2.3	1.7	–	–	V
		I _O = -12 mA	2.7	1.9	–	–	V
		I _O = -24 mA	3.0	2.0	–	–	V
		I _O = -32 mA	4.5	3.4	–	–	V
I _{LI}	input leakage current	V _I = 5.5 V or GND	5.5	–	–	±100	μA
I _{off}	power OFF leakage current	V _I or V _O = 5.5 V	0	–	–	±200	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0 A	5.5	–	–	200	μA
ΔI _{CC}	additional quiescent supply current per pin	V _I = V _{CC} - 0.6 V; I _O = 0 A	2.3 to 5.5	–	–	5000	μA

Note

1. All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

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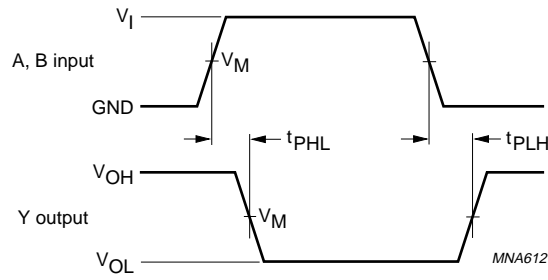
AC CHARACTERISTICSGND = 0 V; $t_r = t_f \leq 2.0$ ns.

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
		WAVEFORMS	V _{CC} (V)				
T_{amb} = -40 °C to +85 °C							
t _{PHL} /t _{PLH}	propagation delay A, B to Y	see Figs 6 and 7	1.65 to 1.95	1.0	3.3	8.0	ns
			2.3 to 2.7	0.5	2.2	5.5	ns
			2.7	0.5	2.6	5.8	ns
			3.0 to 3.6	0.5	2.2	4.7	ns
			4.5 to 5.5	0.5	1.8	4.0	ns
T_{amb} = -40 °C to +125 °C							
t _{PHL} /t _{PLH}	propagation delay A, B to Y	see Figs 6 and 7	1.65 to 1.95	1.0	–	10.5	ns
			2.3 to 2.7	0.5	–	7.0	ns
			2.7	0.5	–	7.5	ns
			3.0 to 3.6	0.5	–	6.0	ns
			4.5 to 5.5	0.5	–	5.5	ns

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AC WAVEFORMS



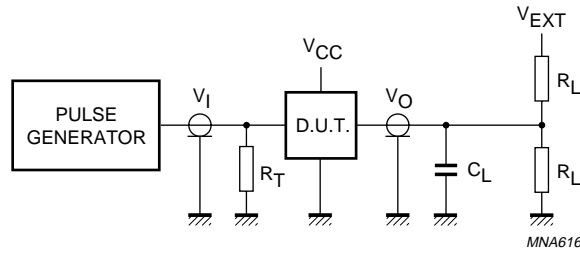
V_{CC}	V_M	INPUT	
		V_I	$t_r = t_f$
1.65 V to 1.95 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.0 ns
2.3 V to 2.7 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.0 ns
2.7 V	1.5 V	2.7 V	≤ 2.5 ns
3.0 V to 3.6 V	1.5 V	2.7 V	≤ 2.5 ns
4.5 V to 5.5 V	$0.5 \times V_{CC}$	V_{CC}	≤ 2.5 ns

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig.6 A, B to Y propagation delay times.

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V _{CC}	V _I	C _L	R _L	V _{EXT}		
				t _{PLH} /t _{PHL}	t _{PZH} /t _{PHZ}	t _{PZL} /t _{PLZ}
1.65 V to 1.95 V	V _{CC}	30 pF	1 kΩ	open	GND	2 × V _{CC}
2.3 V to 2.7 V	V _{CC}	30 pF	500 Ω	open	GND	2 × V _{CC}
2.7 V	2.7 V	50 pF	500 Ω	open	GND	6 V
3.0 V to 3.6 V	2.7 V	50 pF	500 Ω	open	GND	6 V
4.5 V to 5.5 V	V _{CC}	50 pF	500 Ω	open	GND	2 × V _{CC}

Definitions for test circuit:

R_L = Load resistor.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

Fig.7 Load circuitry for switching times.

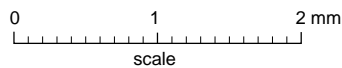
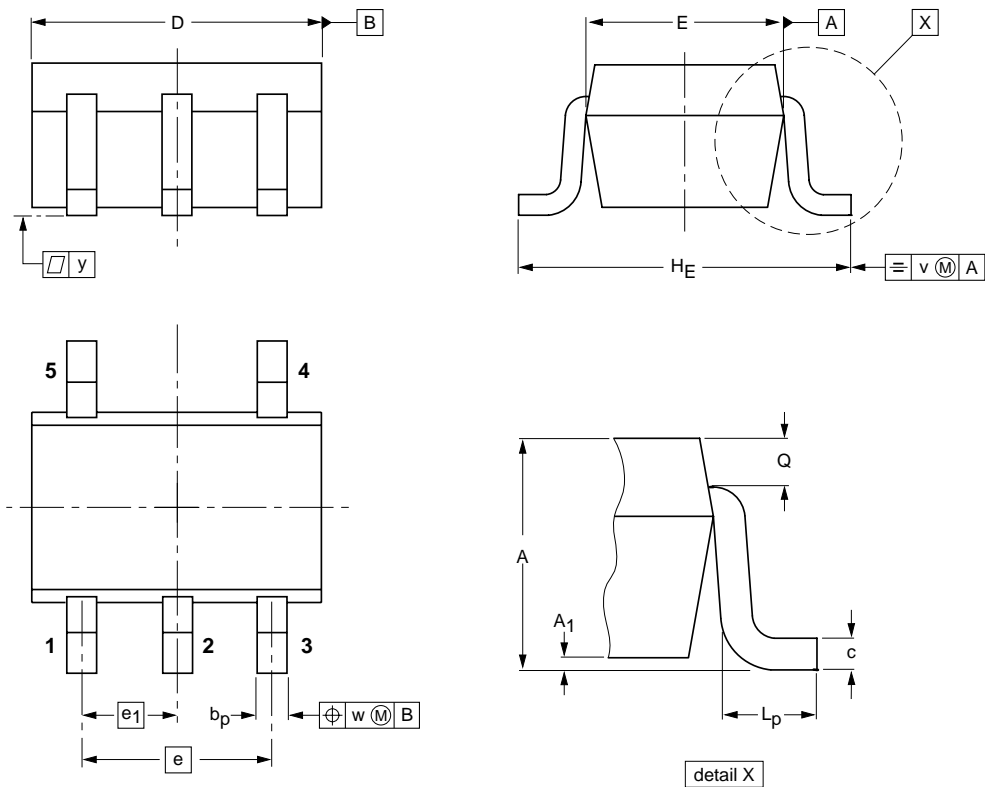
Single 2-input NAND gate

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PACKAGE OUTLINES

Plastic surface mounted package; 5 leads

SOT353



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E (2)	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

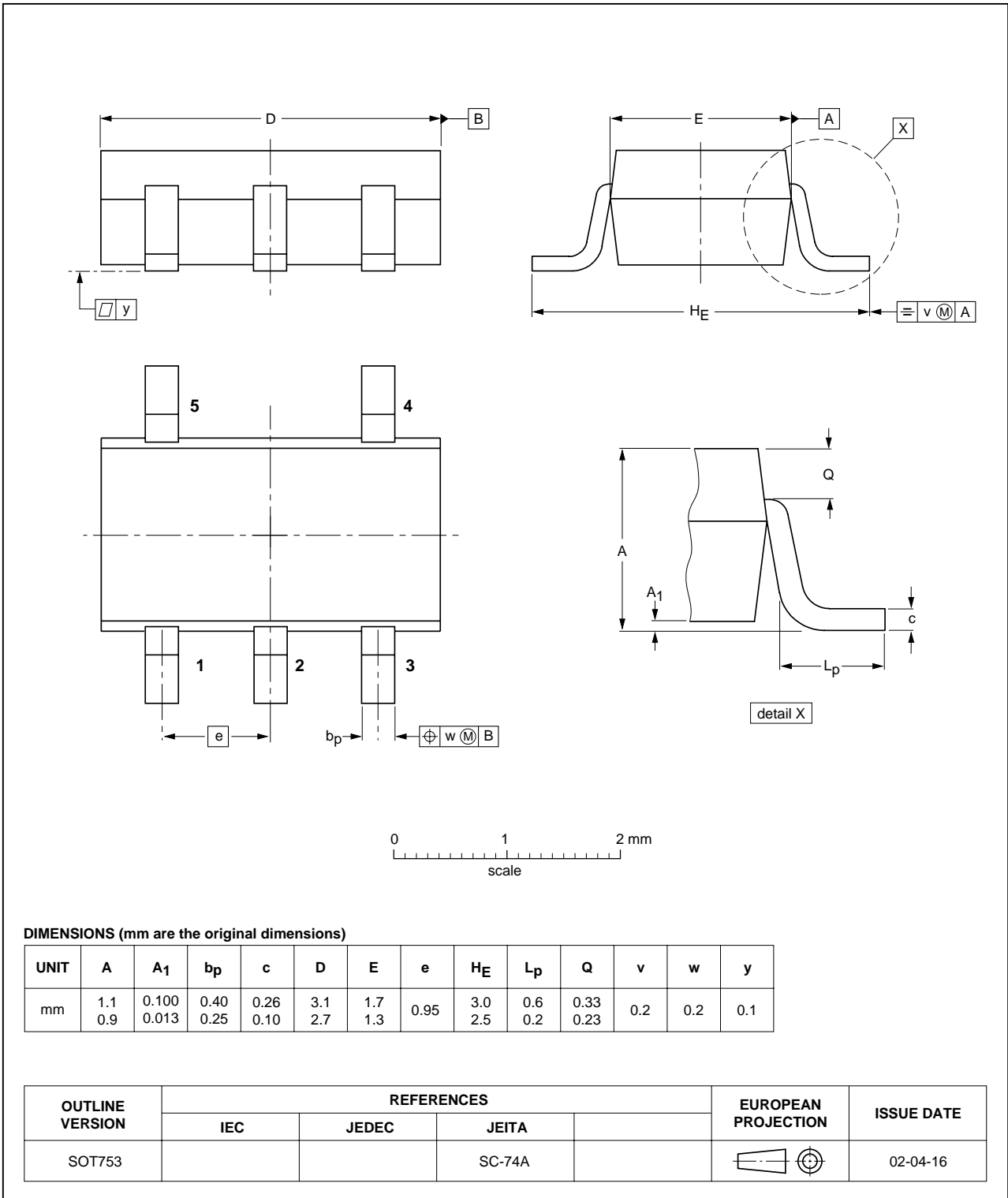
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT353			SC-88A			97-02-28

Single 2-input NAND gate

74LVC1G00

Plastic surface mounted package; 5 leads

SOT753

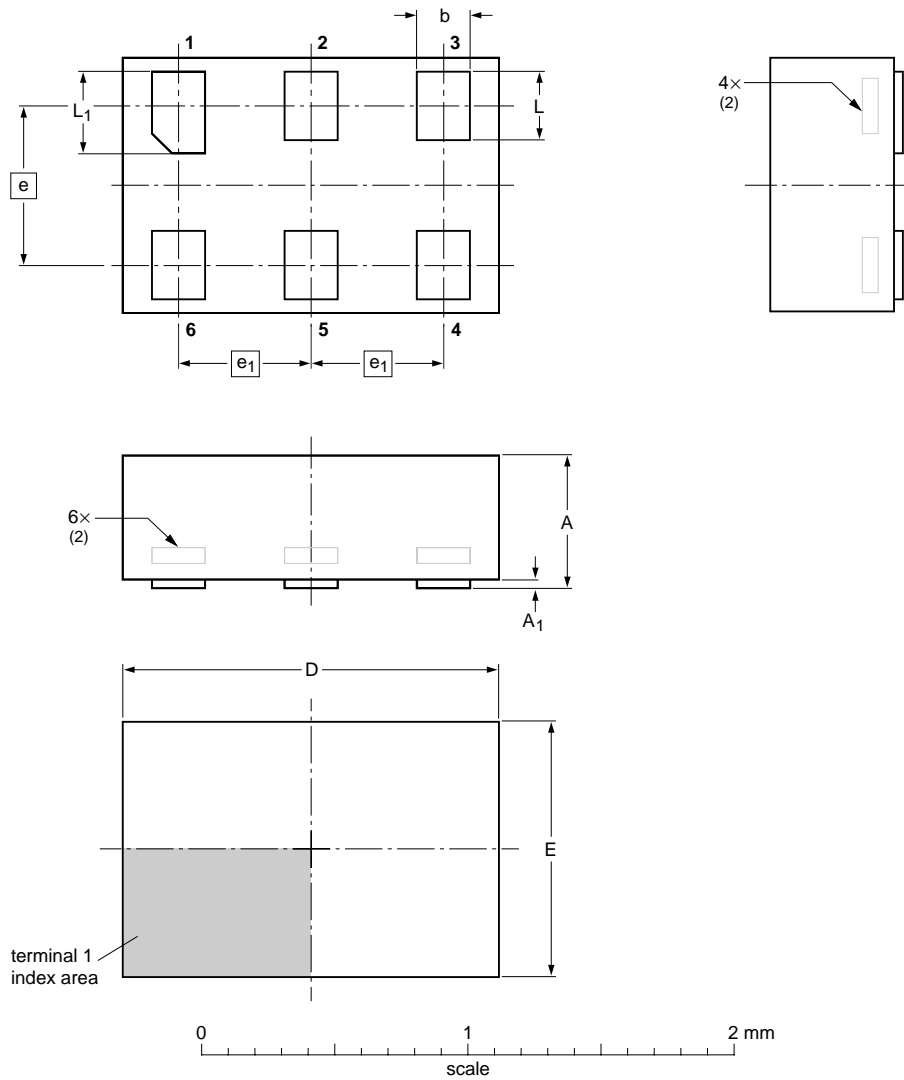


Single 2-input NAND gate

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XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886



DIMENSIONS (mm are the original dimensions)

UNIT	A ⁽¹⁾ max	A ₁ max	b	D	E	e	e ₁	L	L ₁
mm	0.5	0.04	0.25 0.17	1.5 1.4	1.05 0.95	0.6	0.5	0.35 0.27	0.40 0.32

Notes

1. Including plating thickness.
2. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT886		MO-252			04-07-15 04-07-22

Single 2-input NAND gate

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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